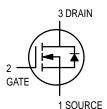
TMOS FET Transistor

N-Channel — Enhancement



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain Source Voltage	V _{DSS}	60	Vdc
Drain–Gate Voltage (R_{GS} = 1.0 M Ω)	V _{DGR}	60	Vdc
Gate–Source Voltage — Continuous — Non–repetitive (t _p ≤ 50 μs)	V _{GS} V _{GSM}	±20 ±40	Vdc Vpk
Drain Current Continuous Pulsed	I _D IDM	200 500	mAdc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	PD	350 2.8	mW mW/°C
Operating and Storage Temperature Range	TJ, Tstg	-55 to +150	°C

¹²³ CASE 29–04, STYLE 22

TO-92 (TO-226AA)

2N7000

Motorola Preferred Device

THERMAL CHARACTERISTICS

Characteristic	Symbol	Мах	Unit
Thermal Resistance, Junction to Ambient	R _{θJA}	357	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/16" from case for 10 seconds	ТL	300	°C

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS		•		
Drain–Source Breakdown Voltage $(V_{GS} = 0, I_D = 10 \mu Adc)$	V _(BR) DSS	60	-	Vdc
Zero Gate Voltage Drain Current (V_{DS} = 48 Vdc, V_{GS} = 0) (V_{DS} = 48 Vdc, V_{GS} = 0, T_{J} = 125°C)	IDSS		1.0 1.0	μAdc mAdc
Gate–Body Leakage Current, Forward (V _{GSF} = 15 Vdc, V _{DS} = 0)	IGSSF	-	-10	nAdc
ON CHARACTERISTICS ⁽¹⁾		•	•	
Gate Threshold Voltage $(V_{DS} = V_{GS}, I_D = 1.0 \text{ mAdc})$	VGS(th)	0.8	3.0	Vdc
Statia Drain Courses On Desistance				Ohm

Static Drain–Source On–Resistance ($V_{GS} = 10 \text{ Vdc}, I_D = 0.5 \text{ Adc}$) ($V_{GS} = 4.5 \text{ Vdc}, I_D = 75 \text{ mAdc}$)	^r DS(on)		5.0 6.0	Ohm
Drain–Source On–Voltage ($V_{GS} = 10$ Vdc, $I_D = 0.5$ Adc) ($V_{GS} = 4.5$ Vdc, $I_D = 75$ mAdc)	VDS(on)	_	2.5 0.45	Vdc

1. Pulse Test: Pulse Width \leq 300 $\mu s,$ Duty Cycle \leq 2.0%.

Preferred devices are Motorola recommended choices for future use and best overall value.

REV 3

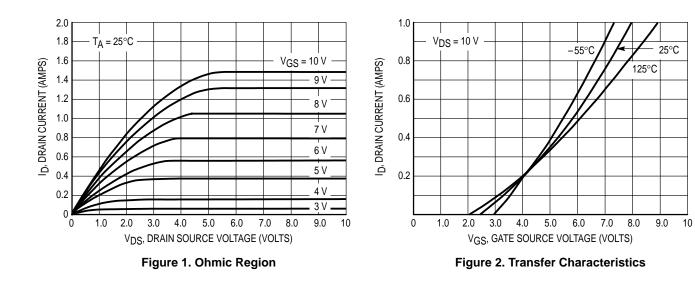


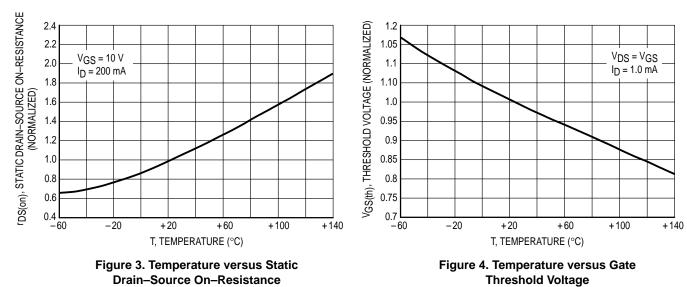
2N7000

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted) (Continued)

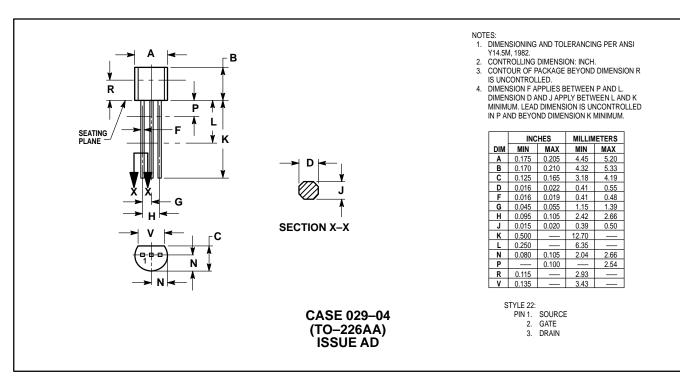
Ch	aracteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS(1) (continued)	•			
On–State Drain Current (V _{GS} = 4.5 Vdc, V _{DS} = 10 Vd	c)	l _{d(on)}	75	-	mAdc
Forward Transconductance (V _{DS} = 10 Vdc, I _D = 200 mAd	c)	9fs	100	-	μmhos
DYNAMIC CHARACTERISTI	cs	•			
Input Capacitance	(V _{DS} = 25 V, V _{GS} = 0, f = 1.0 MHz)	C _{iss}	—	60	pF
Output Capacitance		C _{OSS}	—	25	1
Reverse Transfer Capacitance		C _{rss}	—	5.0	1
SWITCHING CHARACTERIS	TICS(1)				
Turn–On Delay Time	(V _{DD} = 15 V, I _D = 500 mA, R _{gen} = 25 ohms, R _L = 25 ohms)	ton	—	10	ns
Turn–Off Delay Time		toff	—	10	

1. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%.





PACKAGE DIMENSIONS



2N7000

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